

N-channel 30 V 1.7 mΩ logic level MOSFET in LFPAK Rev. 1 — 30 May 2011 Product

Product data sheet

1. **Product profile**

1.1 General description

Logic level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency gains in switching power convertors

1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

Improved mechanical and thermal characteristics

- LFPAK provides maximum power density in a Power SO8 package
- Motor control
- Server power supplies

1.4 Quick reference data

Table 1.	Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	30	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V};$ see <u>Figure 1</u>	[1]	-	-	100	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	109	W
Tj	junction temperature			-55	-	175	°C
Static characteristics							
R_{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 100 °C; see <u>Figure 13</u>		-	-	2.4	mΩ
		V_{GS} = 10 V; I _D = 15 A; T _j = 25 °C		-	1.3	1.7	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	$V_{GS} = 4.5 \text{ V}; \text{ I}_{D} = 10 \text{ A};$ $V_{DS} = 12 \text{ V}; \text{ see } \underline{\text{Figure } 14};$ $\text{see } \underline{\text{Figure } 15}$		-	8.7	-	nC



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Table 1.	Quick reference data continued						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Q _{G(tot)}	total gate charge	V_{GS} = 4.5 V; I_D = 10 A; V_{DS} = 12 V; see <u>Figure 14</u>	-	36.2	-	nC	
Avalanch	e ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy		-	-	241	mJ	

[1] Continuous current is limited by package.

2. Pinning information

Table 2.	Pinning	j information				
Pin	Symbol	Description	Simplified outline	Graphic symbol		
1	S	source				
2	S	source	mb			
3	S	source				
4	G	gate				
mb	D	mounting base; connected to drain	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	mbb076 S		

SOT669 (LFPAK; Power-SO8)

3. Ordering information

Table 3. O	Ordering information					
Type number		Package				
		Name	Description	Version		
PSMN1R7-30	80YL	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669		

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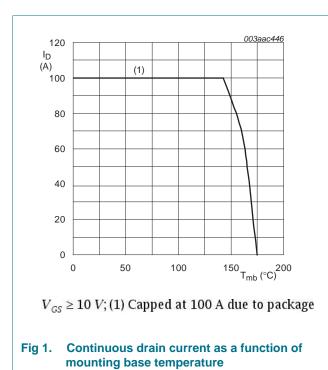
4. Limiting values

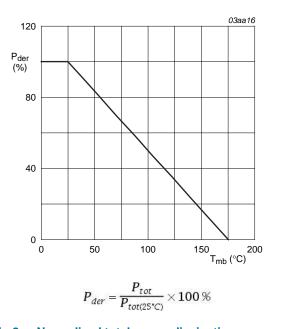
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	30	V
V _{DSM}	peak drain-source voltage	$t_p \le 25 \text{ ns; } f \le 500 \text{ kHz; } E_{DS(AL)} \le 360 \text{ nJ;}$ pulsed		-	35	V
V _{DGR}	drain-gate voltage	T _j ≥ 25 °C; T _j ≤ 175 °C; R _{GS} = 20 kΩ		-	30	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u>	[1]	-	100	А
		V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	[1]	-	100	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3		-	790	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	109	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	in diode					
I _S	source current	T _{mb} = 25 °C	[1]	-	100	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	790	А
Avalanche I	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; $V_{sup} \le$ 30 V; R_{GS} = 50 Ω ; unclamped		-	241	mJ

[1] Continuous current is limited by package.

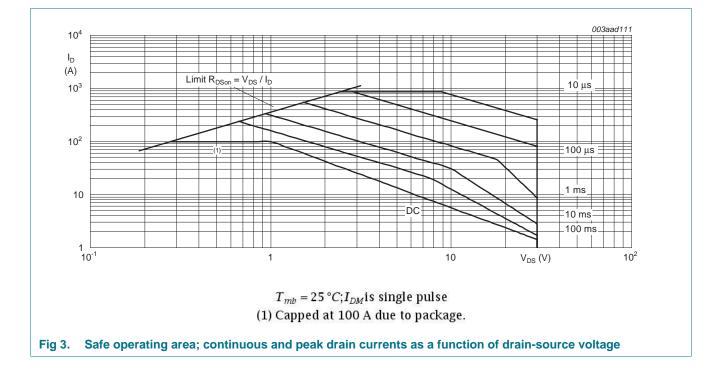






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5. Thermal characteristics

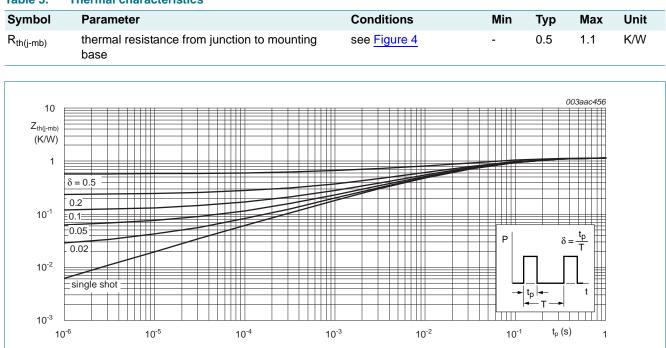


Table 5. Thermal characteristics

Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

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6. Characteristics

Table 6. Characteristics

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS} drain-source breakdown		$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	30	-	-	V
	voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ C$	27	-	-	V
$V_{\text{GS(th)}}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 11</u> ; see <u>Figure 12</u>	1.3	1.7	2.15	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 150 °C; see <u>Figure 12</u>	0.65	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see Figure 12	-	-	2.45	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
		V _{DS} = 30 V; V _{GS} = 0 V; T _i = 150 °C	-	-	100	μA
I _{GSS}	gate leakage current	V _{GS} = 16 V; V _{DS} = 0 V; T _i = 25 °C	-	-	100	nA
		V _{GS} = -16 V; V _{DS} = 0 V; T _i = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 4.5 V; I _D = 15 A; T _j = 25 °C	-	1.8	2.1	mΩ
	resistance	$V_{GS} = 10 \text{ V}; \text{ I}_D = 15 \text{ A}; \text{ T}_j = 150 \text{ °C};$ see Figure 13	-	-	2.8	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 100 °C; see <u>Figure 13</u>	-	-	2.4	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C	-	1.3	1.7	mΩ
R _G	gate resistance	f = 1 MHz	-	0.77	1.5	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	$I_D = 10 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	77.9	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	70	-	nC
		I_D = 10 A; V_{DS} = 12 V; V_{GS} = 4.5 V; see Figure 14	-	36.2	-	nC
Q _{GS}	gate-source charge	I_D = 10 A; V_{DS} = 12 V; V_{GS} = 4.5 V;	-	11.6	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see <u>Figure 14;</u> see <u>Figure 15</u>	-	8	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	3.6	-	nC
Q _{GD}	gate-drain charge		-	8.7	-	nC
V _{GS(pl)}	gate-source plateau voltage	V _{DS} = 12 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	2.34	-	V
C _{iss}	input capacitance	V _{DS} = 12 V; V _{GS} = 0 V; f = 1 MHz;	-	5057	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	1082	-	pF
C _{rss}	reverse transfer capacitance		-	398	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 12 \text{ V}; \text{ R}_{L} = 0.5 \Omega; \text{ V}_{GS} = 4.5 \text{ V};$	-	46	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	72	-	ns
t _{d(off)}	turn-off delay time		-	76	-	ns
t _f	fall time		-	34	-	ns
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Symbol

V_{SD}

Source-drain diode

PSMN1R7-30YL

Typ

0.78

Max

1.2

Unit

V

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Min

$I_{S} = 20 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s};$ t_{rr} reverse recovery time 45 -ns $V_{GS} = 0 V; V_{DS} = 20 V$ recovered charge nC Qr 56 --003aac449 003aac450 300 5 \mathbf{I}_{D} (A) R_{DSor} 10 3.6 $(m\Omega)$ 250 V_{GS} (V) = 3.2 4 $V_{GS}(V) = 3.4$ 200 3 150 3 3.6 2.8 4 100 2 2.6 7 50 24 10 22 0 0 2 4 6 8 10 V_{DS} (V) 0 50 100 150 200 _{I_D (A)} 250 $T_{j} = 25 \,^{\circ}C; t_{p} = 300 \,\mu s$ $T_{i} = 25 \,^{\circ}C; t_{p} = 300 \,\mu s$ Fig 5. Output characteristics: drain current as a Fig 6. of drain current; typical values function of drain-source voltage; typical values 003aac452 003aac455 200 8000 C_{iss} С g_{fs} (pF) (S) 150 6000 100 4000 Crss 50 2000 0 0 20 40 I_D (A) 80 0 60 2 4 6 8 _{VGS} (V) 10 $T_j = 25 \,^{\circ}C; V_{DS} = 15V$ $V_{DS} = 0V; f = 1MHz$ Forward transconductance as a function of Input and reverse transfer capacitances as a Fig 7. Fig 8. drain current; typical values function of gate-source voltage; typical values

Conditions

see Figure 17

I_S = 25 A; V_{GS} = 0 V; T_i = 25 °C;

Characteristics ... continued Table 6.

Parameter

Tested to JEDEC standards where applicable.

source-drain voltage

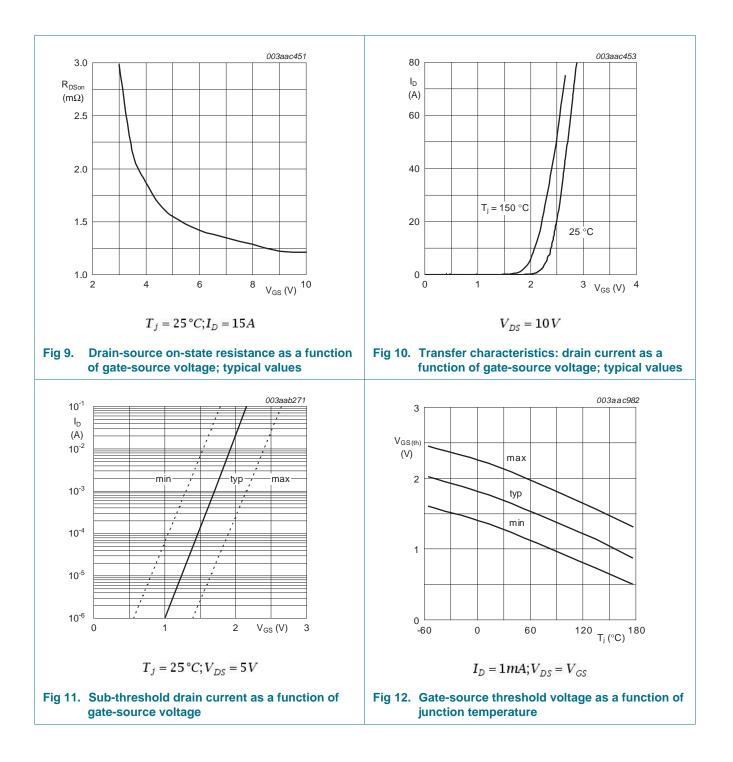
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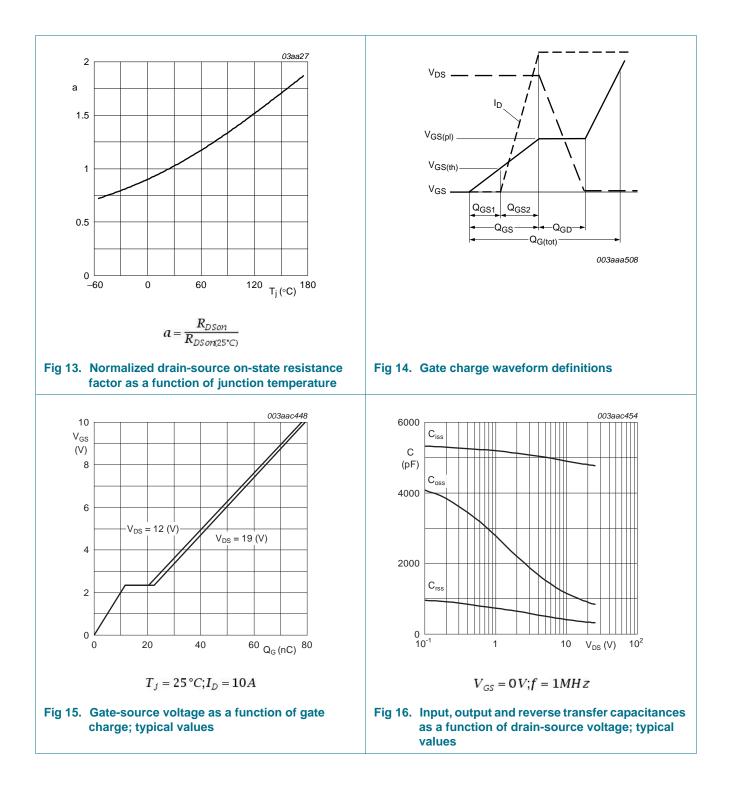
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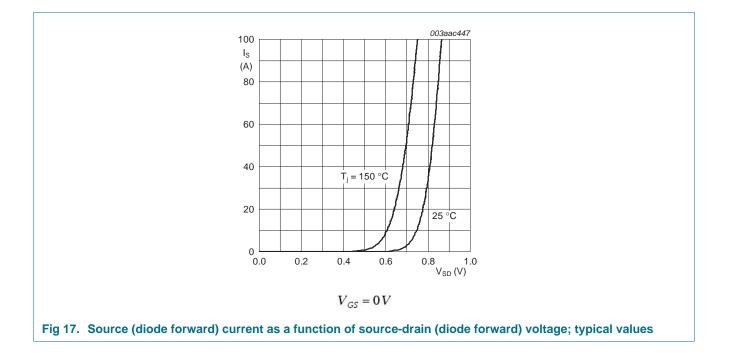
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7. Package outline

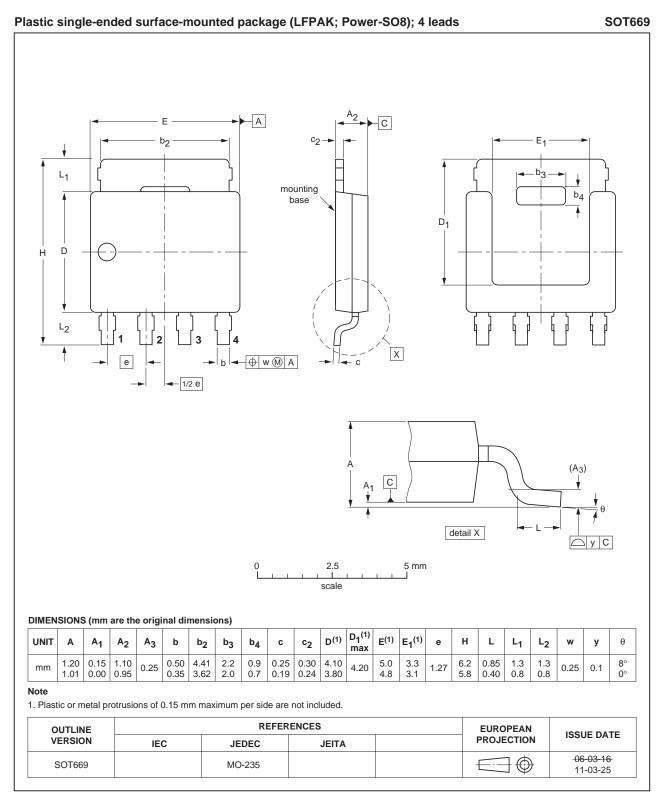


Fig 18. Package outline SOT669 (LFPAK; Power-SO8)

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8. Revision history

Table 7. Revision h	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN1R7-30YL v.5	20110530	Product data sheet	-	PSMN1R7-30YL v.4
Modifications:	 Various changes 	to content.		
PSMN1R7-30YL v.4	20100420	Product data sheet	-	PSMN1R7-30YL v.3

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9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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